

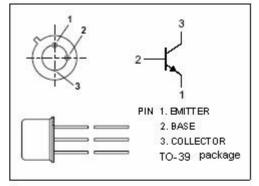
# isc Silicon NPN Planar Epitaxial Overlay Transistor

2N3866

## **DESCRIPTION**

- High Gain Bandwidth Product f<sub>T</sub>= 500 MHz (Min.)
- Low Collector Capacitance;
  C<sub>C</sub> = 3 pF Max.

Minimum Lot-to-Lot variations for robust device performance and reliable operation

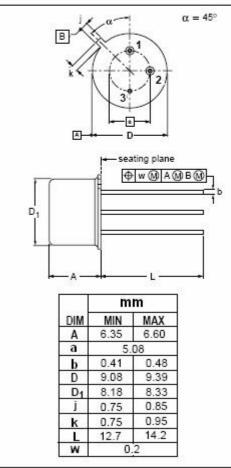


### **APPLICATIONS**

 Designed for use in output, driver or pre-driver stages in VHF and UHF equipment.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	55	V	
V <sub>CER</sub>	Collector-Emitter Voltage R <sub>BE</sub> = 10 Ω	55	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V	
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V	
lc	Collector Current-Continuous	0.4	Α	
Pc	Collector Power Dissipation @T <sub>C</sub> =25℃	3.5	W	
TJ	Junction Temperature	200	${\mathbb C}$	
T <sub>stg</sub>	Storage Temperature Range	-65~+200	$^{\circ}$	





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>B</sub> = 0	30			V
$V_{(BR)CER}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; R <sub>BE</sub> = 10 Ω	55			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	l <sub>C</sub> = 0.1mA; l <sub>E</sub> = 0	55			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 0.1mA; I <sub>C</sub> = 0	3.5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 100mA; I <sub>B</sub> = 20mA			1.0	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 28V; I <sub>B</sub> = 0			20	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 50mA ; V <sub>CE</sub> = 5V	10		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 360mA ; V <sub>CE</sub> = 5V	5			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 50mA; V <sub>CE</sub> = 15V,f = 200MHz	500			MHz
C <sub>C</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 28V; f= 1MHz			3	pF

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